

SIKA e-SiC® 3.5N FCP07

Product information



High-purity silicon carbide powder for semiconductor and electronic applications

High-purity silicon carbide, manufactured using the Acheson process, is utilized in the semiconductor industry for a wide range of components and devices, including wafer boats, paddles, tubes, flanges, and more.

Typical chemistry

Char. description	Unit	Value
PSD instrument		Sedigraph
ds 15%	µm	0,5
ds 50%	µm	2,1
ds 95%	µm	8,3
pH	-	5,0
Surface Area	m ² /g	6,7
Conductivity	µS/cm	7,8
Free C	%	0,3
Free Si	%	0,1
Total O ₂	%	0,9
Al	ppm	73
Fe	ppm	333
Ni	ppm	56
V	ppm	94
Ti	ppm	23
B	ppm	1
Cr	ppm	18
Cu	ppm	1
S	ppm	9
Zn	ppm	0,4
Li	ppm	<0,05

Analytical procedures:

All measurement is in accordance to FEPA, ANSI or JIS, or other methods in agreement with customers. Trace element analysis by GDMS.

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